

## DESCRIPTION

2SC6046 is a silicon NPN epitaxial type transistor designed with high collector current, low  $V_{CE(sat)}$ .

## FEATURE

- High collector current

$I_{C(MAX)}=600\text{mA}$

- Low collector to emitter saturation voltage

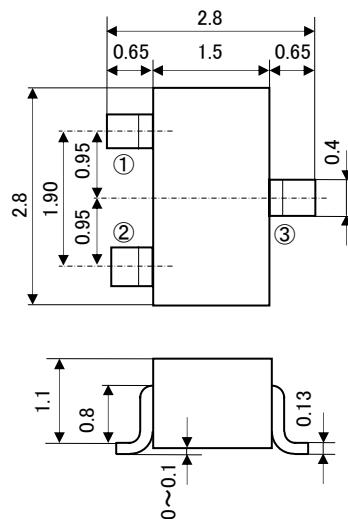
$V_{CE(sat)} < 0.3V_{max}$  ( $IC=150\text{mA}$ ,  $IB=15\text{mA}$ )

## APPLICATION

For switching application, small type motor drive application.

## OUTLINE DRAWING

Unit: mm



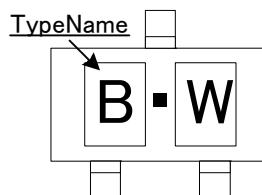
## TERMINAL CONNECTOR

①:BASE EIAJ:SC-59  
 ②:EMITTER JEDEC:Similar to  
 ③:COLLECTOR TO-236

MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ )

Symbol	Parameter	Limits	Unit
$V_{CEO}$	Collector to Emitter voltage	40	V
$V_{CBO}$	Collector to Base voltage	75	V
$V_{EBO}$	Emitter to Base voltage	6	V
$I_C$	Collector current	600	mA
$P_c$	Collector dissipation	200	mW
$T_j$	Junction temperature	+150	°C
$T_{stg}$	Storage temperature	-55~+150	°C

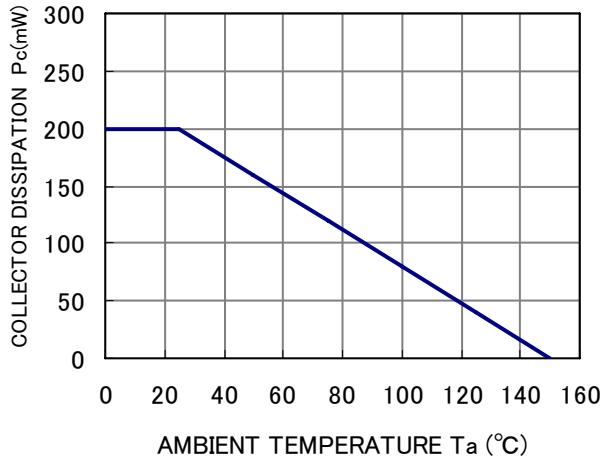
## MARKING

ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ )

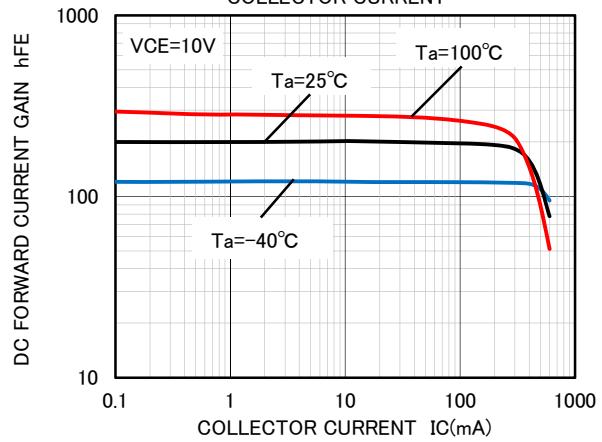
Symbol	Parameter	Test condition	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CEO}$	C to E breakdown voltage	$IC=1\text{mA}$ , $IB=0$	40	—	—	V
$V_{(BR)CBO}$	C to B breakdown voltage	$IC=10\text{\mu A}$ , $IE=0$	75	—	—	V
$V_{(BR)EBO}$	E to B breakdown voltage	$IE=10\text{\mu A}$ , $IC=0$	6	—	—	V
$I_{CBO}$	Collector cut off current	$VCB=60\text{V}$ , $IE=0$	—	—	100	nA
$I_{EBO}$	Emitter cut off current	$VEB=3\text{V}$ , $IC=0$	—	—	100	nA
$h_{FE}$	DC forward current gain	$IC=150\text{mA}$ , $VCE=10\text{V}$	100	—	300	—
$V_{CE(sat)}$	C to E saturation voltage	$IC=150\text{mA}$ , $IB=15\text{mA}$	—	—	0.3	V
$V_{BE(sat)}$	B to E saturation voltage	$IC=150\text{mA}$ , $IB=15\text{mA}$	0.6	—	1.2	V
$f_T$	Gain band width product	$IE=-20\text{mA}$ , $VCE=20\text{V}$ , $f=100\text{MHz}$	—	250	—	MHz
$C_{ob}$	Collector output capacitance	$VCB=10\text{V}$ , $f=1\text{MHz}$	—	—	8	pF

## TYPICAL CHARACTERISTICS

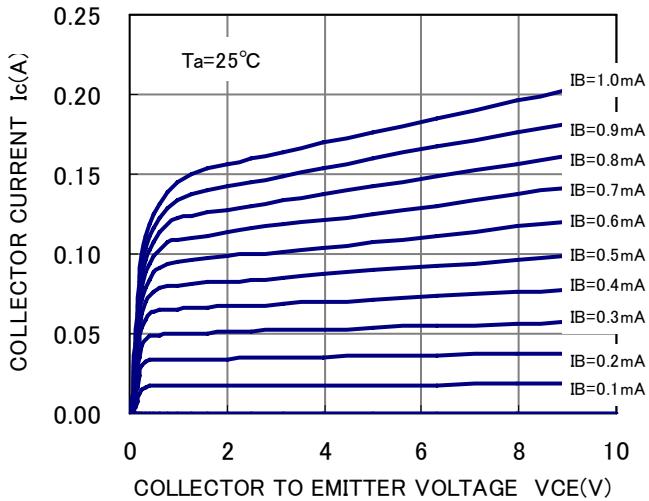
COLLECTOR DISSIPATION VS.  
AMBIENT TEMPERATURE



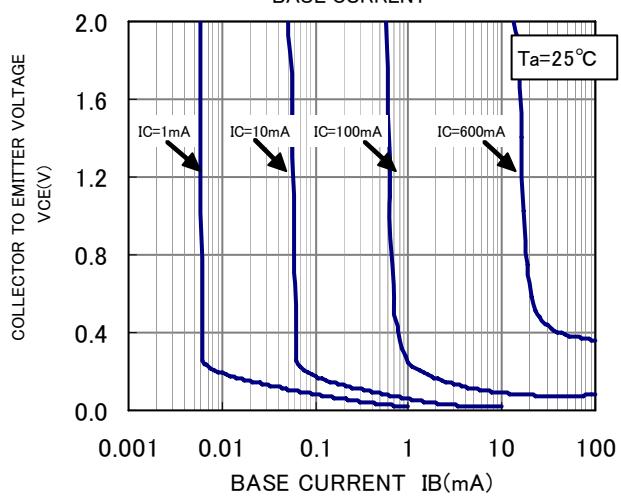
DC FORWARD CURRENT GAIN VS.  
COLLECTOR CURRENT



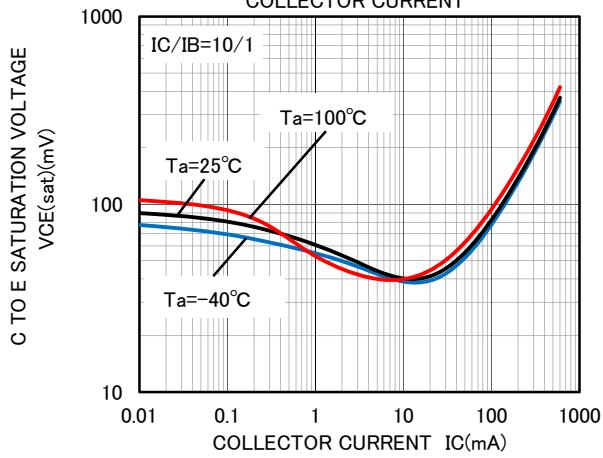
COMMON Emitter Output



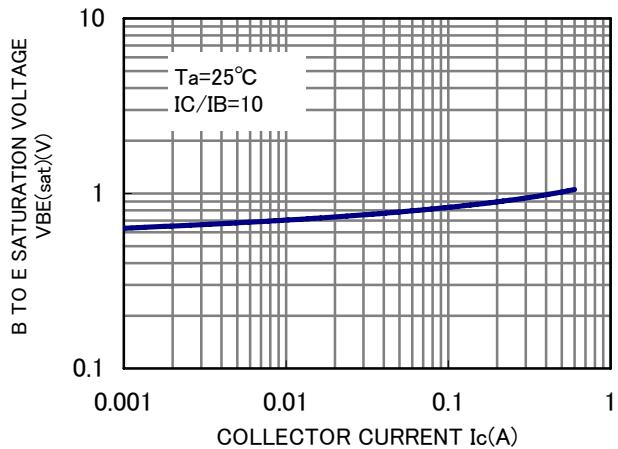
COLLECTOR TO Emitter VOLTAGE VS.  
BASE CURRENT



C TO E SATURATION VOLTAGE VS.  
COLLECTOR CURRENT



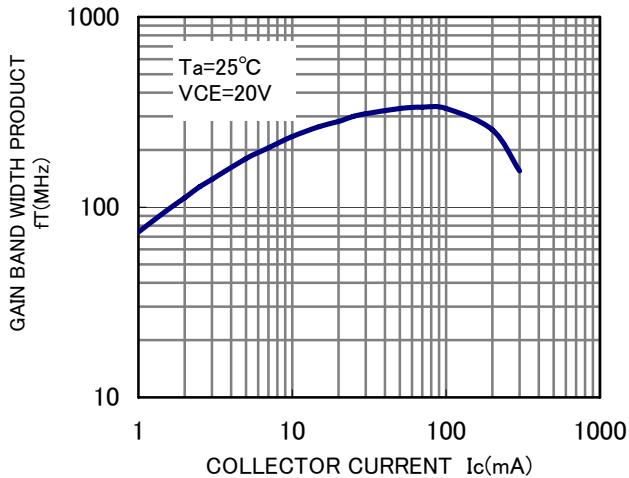
B TO E SATURATION VOLTAGE VS.  
COLLECTOR CURRENT



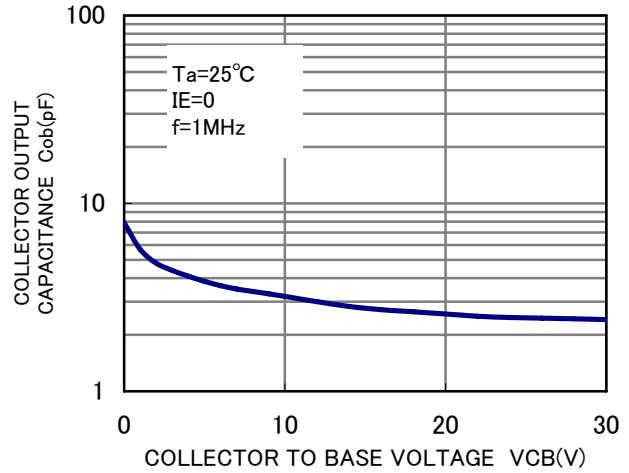
# 2SC6046-T150

FOR GENERAL PURPOSE HIGH CURRENT DRIVE APPLICATION  
SILICON NPN EPITAXIAL TYPE

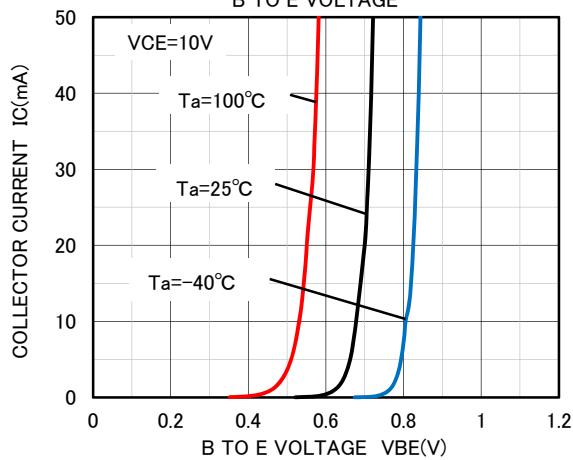
GAIN BAND WIDTH PRODUCT VS.  
COLLECTOR CURRENT



COLLECTOR OUTPUT CAPACITANCE VS.  
COLLECTOR TO BASE VOLTAGE



COLLECTOR CURRENT VS.  
B TO E VOLTAGE



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